



Absolute Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	200	V
Collector-Emitter Voltage	V _{CEO}	100	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	6	А
Peak Pulse Current	I _{CM}	10	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Note 5)		3.2		
Power Dissipation	(Note 6)	P_{D}	1.7	W	
	(Note 7)		0.74		
	(Note 5)		39 R _{0JA} 75		
Thermal Resistance, Junction to Ambient Air	(Note 6)	R _{0JA}			
	(Note 7)		169	°C/W	
Thermal Resistance, Junction to Leads	(Note 8)	$R_{ heta JL}$	5.6		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with the exposed collector pad on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

 6. Same as note (5), except mounted on 25mm x 25mm 1oz copper.

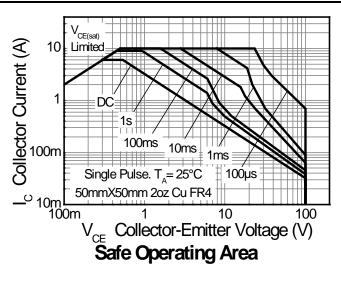
 7. Same as note (5), except mounted on minimum recommended pad (MRP) layout.

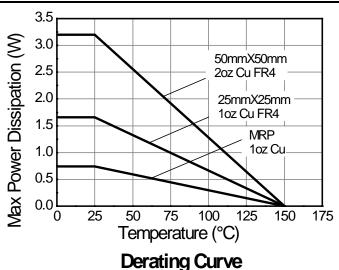
 8. Thermal resistance from junction to solder-point (on the exposed collector pad).

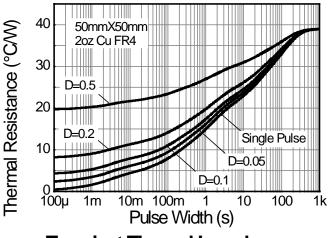
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

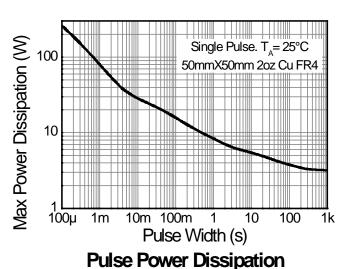


Thermal Characteristics and Derating Information

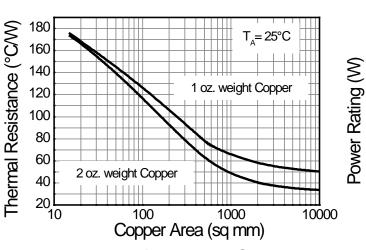








Transient Thermal Impedance



T_A= 25°C

2 oz. weight Copper

1 oz. weight Copper

10 100 1000 10000

Thermal Resistance vs. Cu Area

Power Rating vs. Cu Area

Copper Area (sq mm)





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

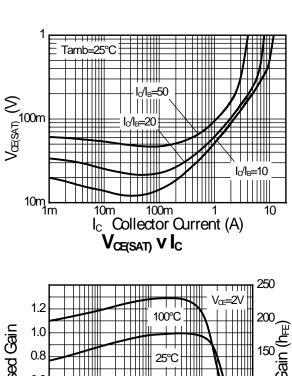
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	200	235	_	>	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	100	115	_	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.1	_	V	$I_E = 100 \mu A$
Collector Cutoff Current	I _{CBO}	1 1	_	20 0.5	nΑ μΑ	V _{CB} = 150V V _{CB} = 150V, T _{AMB} = 100°C
Collector Cutoff Current	I _{CER} R≤1kΩ		_ _	20 0.5	nΑ μΑ	V _{CB} = 150V V _{CB} = 150V, T _{AMB} = 100°C
Emitter Cutoff Current	I _{EBO}	_		10	nA	V _{EB} = 6V
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(sat)}	_ _ _	21 50 95 180	35 65 125 220	mV	$I_C = 0.1A$, $I_B = -5mA$ $I_C = 1A$, $I_B = 100mA$ $I_C = 2A$, $I_B = 100mA$ $I_C = 5A$, $I_B = 500mA$
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}	_	1020	1120	mV	$I_C = 5A$, $I_B = 500mA$
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(on)}	_	920	1000	mV	$V_{CE} = 2V$, $I_C = 5A$
DC Current Gain (Note 10)	h _{FE}	100 100 30 10	_ _ _	300 — —	_	V _{CE} = 2V, I _C = 10mA V _{CE} = 2V, I _C = 2A V _{CE} = 2V, I _C = 5A V _{CE} = 2V, I _C = 10A
Transition Frequency	f _T	1	130	_	MHz	V _{CE} = 10V, I _C = 100mA, f = 50MHz
Output Capacitance	C _{obo}		26	_	pF	V _{CB} = 10V, f = 1MHz
Switching Times	t _{on} t _{off}	_ _	41 1010	_ _	ns	$V_{CC} = 10V, I_C = 1A,$ $I_{B1} = I_{B2} = 100mA$

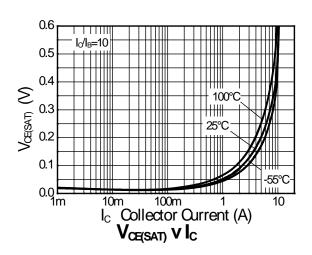
Note: 10. Pulse Test: Pulse width \leq 300 $\mu s.$ Duty cycle \leq 2.0%.

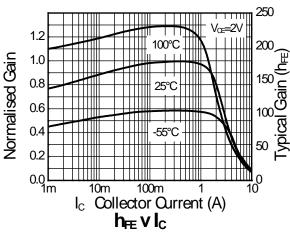


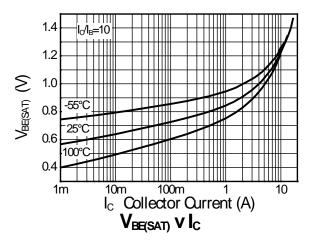


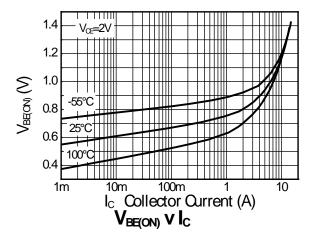
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)







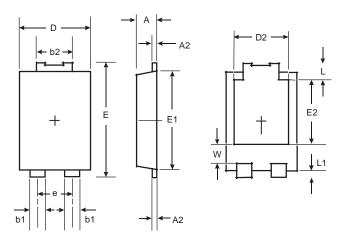






Package Outline Dimensions

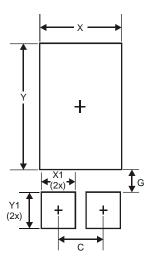
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



POWERDI5				
Dim	Min	Max		
Α	1.05	1.15		
A2	0.33	0.43		
b1	0.80	0.99		
b2	1.70	1.88		
D	3.90	4.05		
D2	3.054 Typ			
Е	6.40	6.60		
е	1.84 Typ			
E1	5.30	5.45		
E2	3.549 Typ			
L	0.75	0.95		
L1	0.50	0.65		
W	1.10	1.41		
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	1.840
G	0.852
Х	3.360
X1	1.390
Y	4.860
Y1	1.400

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.





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